Ordering number:EN1207A

NPN Triple Diffused Planar Silicon Transistor

2SC3277

400V/10A Switching Regulator Applications

Features

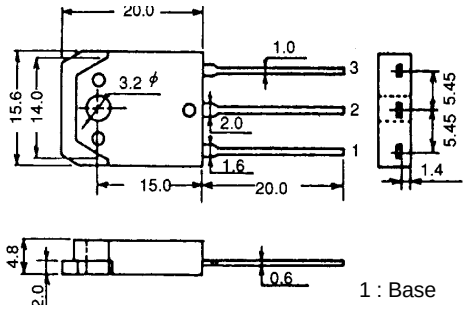
- High breakdown voltage, high current.
- Wide ASO.
- Fast switching speed.

Package Dimensions

unit:mm

2022A

[2SC3277]



1 : Base
2 : Collector
3 : Emitter
SANYO : TO-3PB

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		500	V
Collector-to-Emitter Voltage	V_{CEO}		400	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		10	A
Collector Current (Pulse)	I_{CP}	PW≤300μs, Duty Cycle≤10%	20	A
Collector Dissipation	P_C	Tc=25˚C	90	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=400V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC Current Gain	$h_{FE}1$	V_{CE}=5V, I_C=1.2A	15*		50*	
	$h_{FE}2$	V_{CE}=5V, I_C=6A	8			
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=1.2A		20		MHz
Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz		120		pF

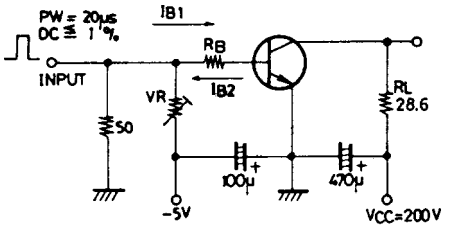
* : The $h_{FE}1$ of the 2SC3277 is classified as follows. When specifying the $h_{FE}1$ rank, specify two ranks or more in principle.

15 L 30	20 M 40	30 N 50

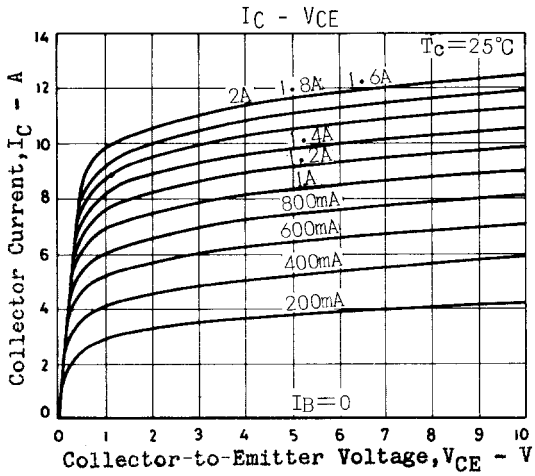
SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

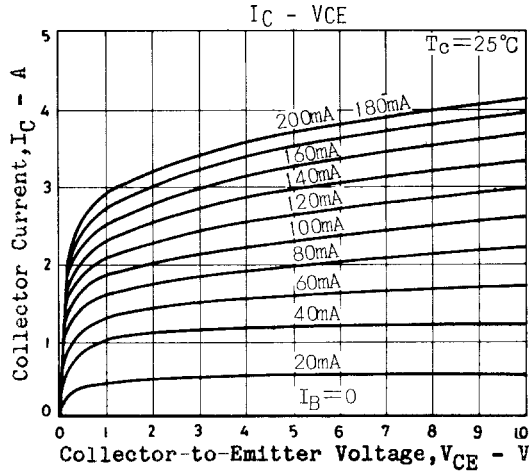
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=6A, I_B=1.2A			1.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=6A, I_B=1.2A			1.5	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	500			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=5mA, R_{BE}=∞	400			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	7			V
Collector-to-Emitter Sustain Voltage	$V_{CEO(sus)}$	I_C=10A, I_B=2A, L=50μH	400			V
Collector-to-Emitter Sustain Voltage	$V_{CEX(sus)1}$	I_C=10A, I_{B1}=2A, L=200μH, I_{B2}=–2A, clamped	400			V
	$V_{CEX(sus)2}$	I_C=2.5A, I_{B1}=0.5A, L=200μH, I_{B2}=–0.5A, clamped	450			V
Turn-ON Time	t_{on}	I_C=7A, I_{B1}=1.4A, I_{B2}=–1.4A, R_L=28.6Ω, V_{CC}=200V			1.0	μs
Storage Time	t_{stg}	I_C=7A, I_{B1}=1.4A, I_{B2}=–1.4A, R_L=28.6Ω, V_{CC}=200V			2.5	μs
Fall Time	t_f	I_C=7A, I_{B1}=1.4A, I_{B2}=–1.4A, R_L=28.6Ω, V_{CC}=200V			1.0	μs

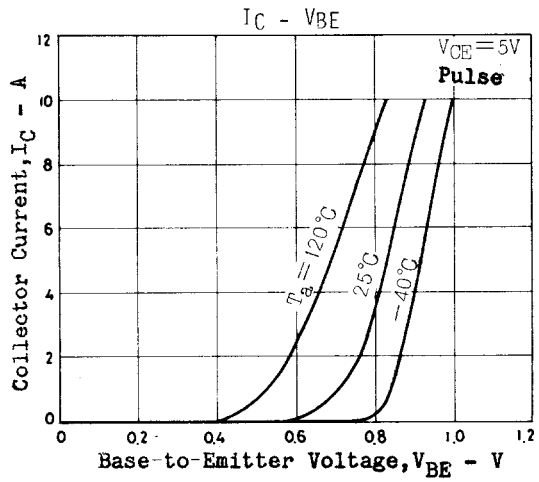
Switching Time Test Circuit

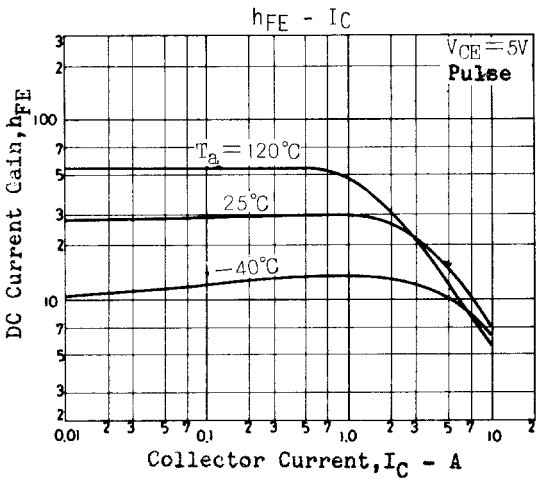


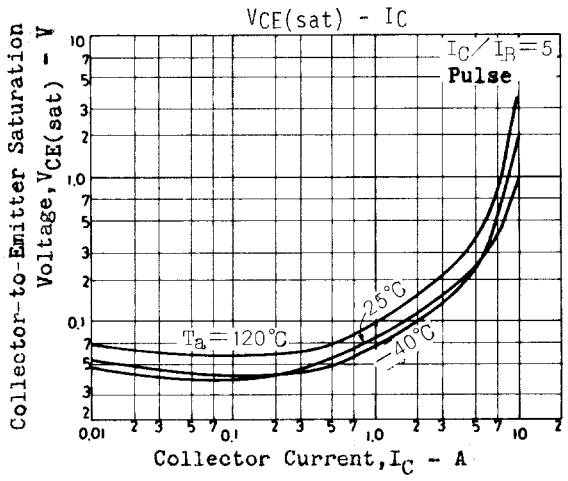
Unit (resistance : Ω, capacitance : F)

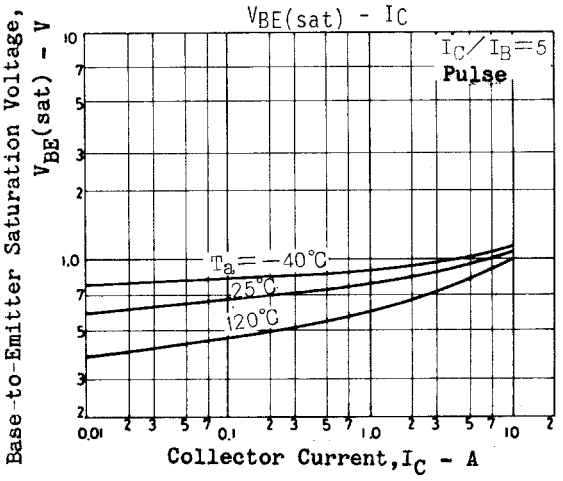


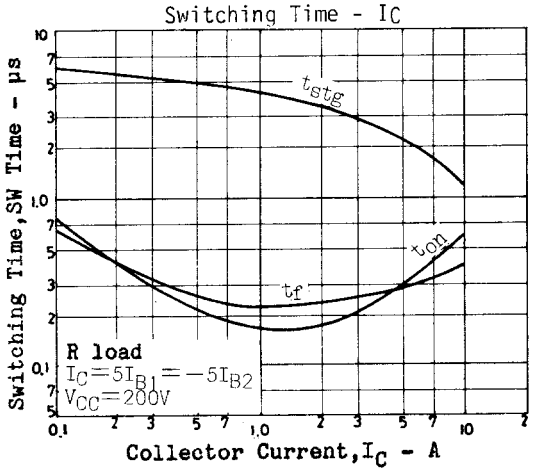


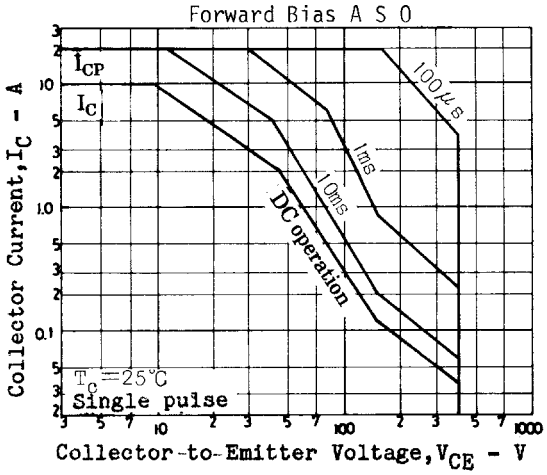


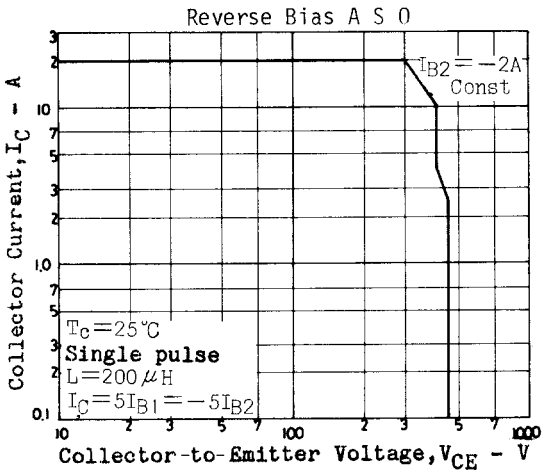


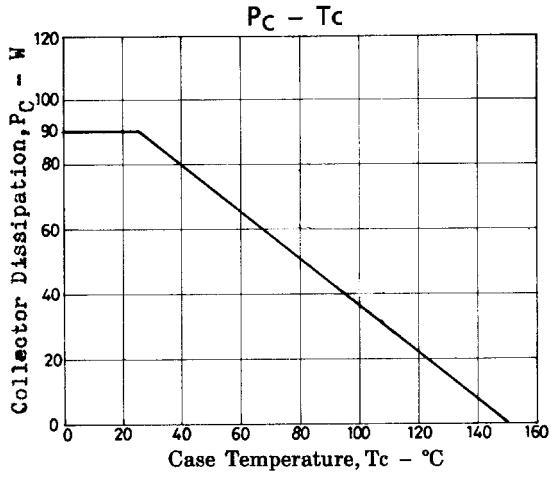

VCE(sat) - IC
IC/IB=5
Pulse
Ta=120°C
25°C
−40°C
Collector-to-Emitter Saturation Voltage, VCE(sat) - V
Collector Current, IC - A


VBE(sat) - IC
IC/IB=5
Pulse
Ta=−40°C
25°C
120°C
Base-to-Emitter Saturation Voltage, VBE(sat) - V
Collector Current, IC - A


Switching Time - IC
tstg
ton
tf
R load
IC=5IB1=−5IB2
VCC=200V
Switching Time, SW Time - μs
Collector Current, IC - A


Forward Bias A S O
ICP
IC
100μs
1ms
10ms
DC operation
Tc=25°C
Single pulse
Collector Current, IC - A
Collector-to-Emitter Voltage, VCE - V


Reverse Bias A S O
IB2=−2A
Const
Tc=25°C
Single pulse
L=200μH
IC=5IB1=−5IB2
Collector Current, IC - A
Collector-to-Emitter Voltage, VCE - V


PC - Tc
Collector Dissipation, PC - W
Case Temperature, Tc - °C